

## **P R E S S   R E L E A S E**

### **X-FAB Announces First 0.35 Micrometer 100V High-Voltage Pure-Play Foundry Technology and Shrinks Silicon Footprint of Existing Devices**

***New operating voltage range from 45-to-100-volts supports lithium ion battery management, Power over Ethernet, piezo drivers for inkjet and ultrasonic imaging, and other emerging high-growth applications***

**Erfurt, Germany, July 15, 2010.** X-FAB Silicon Foundries, the leading analog/mixed-signal foundry and expert in “More than Moore” technologies, today announced the industry’s first 100V high-voltage 0.35 micrometer foundry process. It enables a new class of reliable, high-performing battery monitoring and protection systems for battery management. It also is ideal for power management applications and for ultrasonic imaging and inkjet print head apps using piezoelectric drivers. In addition, X-FAB added new and enhanced N- and P-type double-diffused metal-oxide-semiconductor (DMOS) transistors with 45 percent lower on-resistance for multiple operating voltages up to 100V, lowering the silicon footprint by up to 40 percent and thus reducing die costs. X-FAB will thoroughly discuss these new capabilities in a free webinar, “Addressing High-Voltage Applications with the Industry’s First 0.35 Micrometer 100V Pure-Play Foundry Process,” offered worldwide on July 27 and 28.

Jens Kosch, CTO at X-FAB, said, “The growing popularity of renewable energy sources for hybrid and electric cars, photo-voltaic cells and wind turbines mandates safe, high-performing energy storage management solutions. Using X-FAB’s new specialized high-voltage process, our customers can address these and other emerging applications that present significant growth potential, at lower costs. We see a lot of interest in power management solutions for lithium ion batteries by major car manufacturers around the world, for example. With X-FAB’s new HV process, they can achieve safer, higher performing battery monitoring and protection systems.”

## **Lower cost per function**

X-FAB's new and enhanced N- & P-type DMOS transistors with gate oxide thicknesses of 14nm or 40nm offer customers the choice of 5V or 12V drive capability for their applications with operating voltages of 55V, 75V and 100V. By considerably reducing the on-resistance, integrating into the baseline process an EEPROM function for trimming and program storage, and having a thick metal layer available as the third metal layer, X-FAB has lowered the cost per function significantly. In addition, newly added isolated 5V NMOS and PMOS devices can float between ground and the maximum operating voltage of 100V. Other device enhancements include Schottky diodes, 20V and 100V high-voltage capacitors, and bipolar transistors.

## **Availability**

All of the functions and devices mentioned above are available now as part of X-FAB's 0.35 micrometer high-voltage process offering (XH035).

## **About X-FAB**

X-FAB is the leading analog/mixed-signal foundry group manufacturing silicon wafers for analog-digital integrated circuits (mixed-signal ICs). X-FAB maintains wafer production facilities in Erfurt and Dresden (Germany), Lubbock, Texas (US) and Kuching, Sarawak (Malaysia), and employs approximately 2,400 people worldwide. Wafers are manufactured based on advanced modular CMOS and BiCMOS processes with technologies ranging from 1.0 to 0.18 micrometers for applications primarily in the automotive, communications, consumer and industrial sectors. For more information, please visit [www.xfab.com](http://www.xfab.com).

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